

RJK60S1DPD

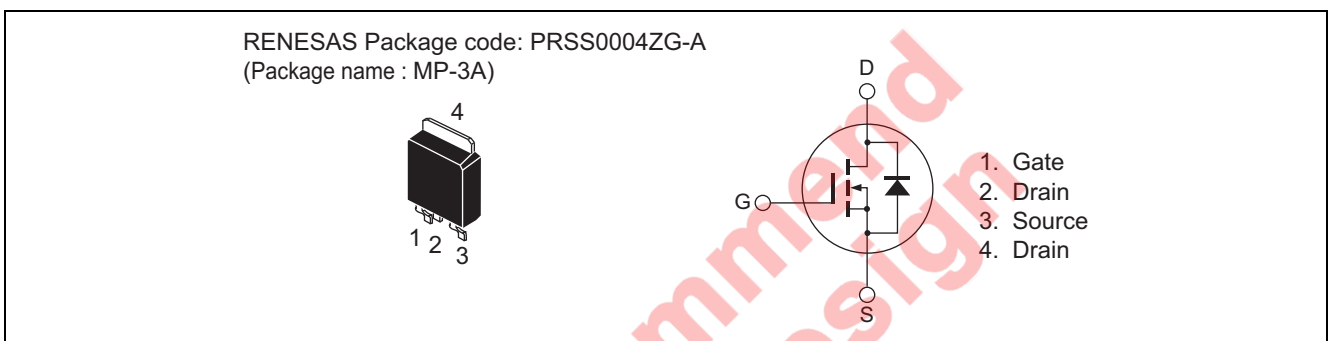
600V - 8A - SJ MOS FET
High Speed Power Switching

R07DS0853EJ0004
Rev.0.04
Nov 30, 2012

Features

- Superjunction MOSFET
- Low on-resistance
 $R_{DS(on)} = 0.84 \Omega$ typ. (at $I_D = 2.2A$, $V_{GS} = 10 V$, $T_a = 25^\circ C$)
- High speed switching
 $t_f = 61 ns$ typ. (at $I_D = 2.2 A$, $V_{GS} = 10 V$, $R_L = 136 \Omega$, $R_g = 10 \Omega$, $T_a = 25^\circ C$)

Outline



Absolute Maximum Ratings

($T_a = 25^\circ C$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	600	V
Gate to source voltage	V_{GSS}	+30, -20	V
Drain current	$T_c = 25^\circ C$	I_D ^{Note1,2}	8 A
	$T_c = 100^\circ C$	I_D ^{Note1,2}	5 A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	16	A
Body-drain diode reverse drain current	I_{DR} ^{Note1}	8	A
Body-drain diode reverse drain peak current	$I_{DR(pulse)}$ ^{Note1}	16	A
Avalanche current	I_{AP} ^{Note3}	1.1	A
Avalanche energy	E_{AR} ^{Note3}	0.066	mJ
Channel dissipation	P_{ch} ^{Note4}	31.2	W
Channel to cse thermal impedance	θ_{ch-c}	4.0	$^\circ C/W$
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

- Notes: 1. Limited by T_{ch} max.
2. Maximum duty cycle $D = 0.5$
3. $ST_{ch} = 25^\circ C$, $T_{ch} \leq 150^\circ C$
4. Value at $T_c = 25^\circ C$

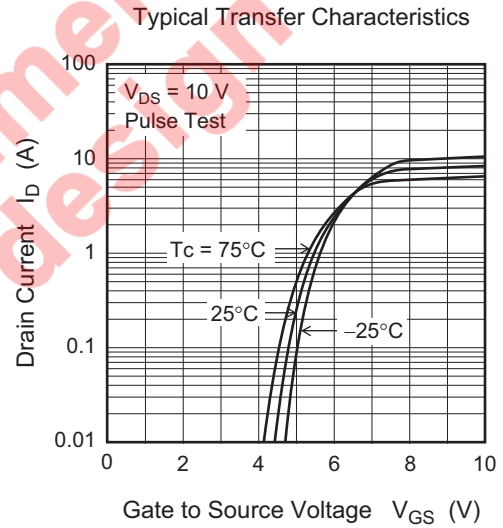
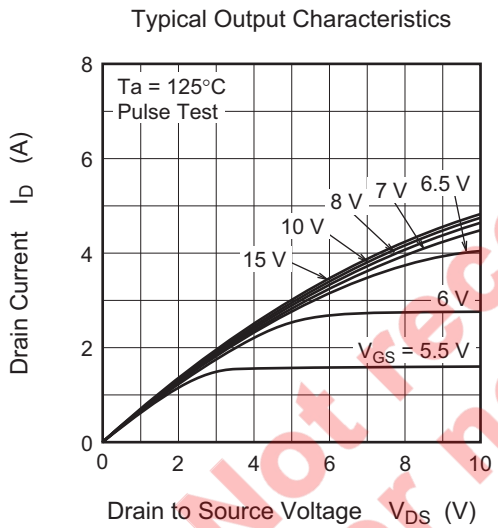
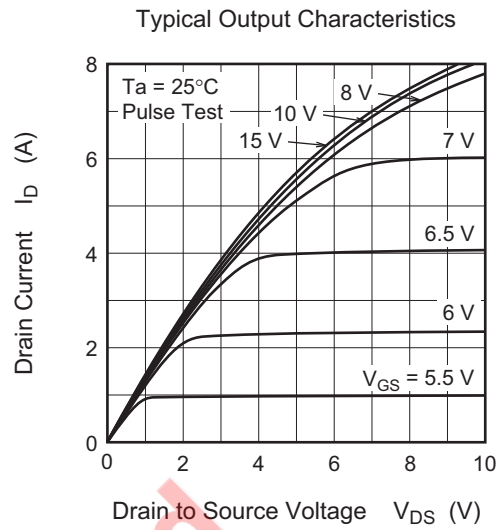
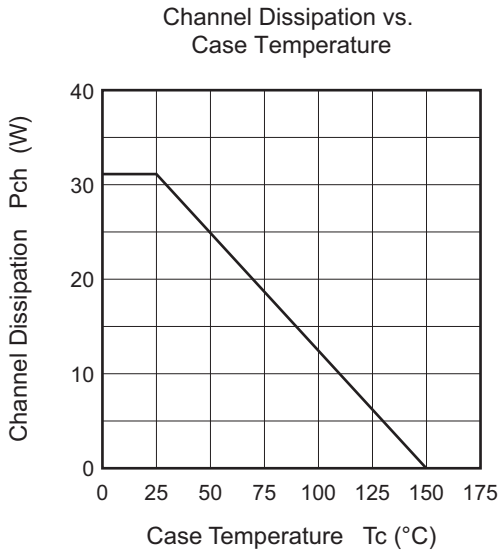
Electrical Characteristics

(Ta = 25°C)

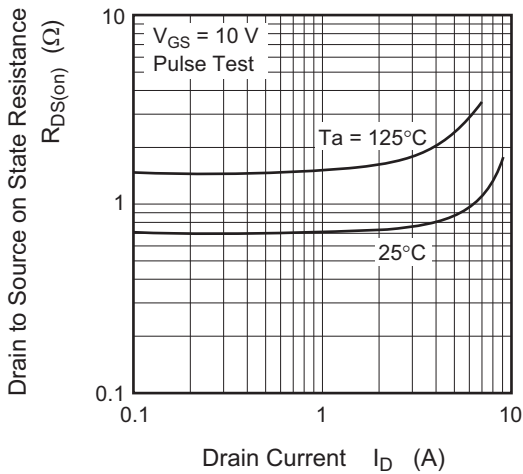
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	mA	$V_{DS} = 600 \text{ V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = +30\text{V}$, -20 V , $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3	—	5	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.84	1.05	Ω	$I_D = 2.2 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note5}
	$R_{DS(on)}$	—	2.10	—	Ω	Ta = 150°C $I_D = 2.2 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note5}
Gate resistance	Rg	—	3.4	—	Ω	f = 1 MHz $V_{DS} = 25 \text{ V}$, $V_{GS} = 0$
Input capacitance	Ciss	—	380	—	pF	$V_{DS} = 25 \text{ V}$
Output capacitance	Coss	—	500	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	2.1	—	pF	f = 100 kHz
Turn-on delay time	$t_{d(on)}$	—	9	—	ns	$I_D = 2.2 \text{ A}$
Rise time	t_r	—	15	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	22	—	ns	$R_L = 136 \Omega$
Fall time	t_f	—	61	—	ns	Rg = 10 Ω ^{Note5}
Total gate charge	Qg	—	9.3	—	nC	$V_{DD} = 480 \text{ V}$
Gate to source charge	Qgs	—	2.1	—	nC	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Qgd	—	4.5	—	nC	$I_D = 1 \text{ A}$ ^{Note5}
Body-drain diode forward voltage	V_{DF}	—	1.0	1.6	V	$I_F = 4.4 \text{ A}$, $V_{GS} = 0$ ^{Note5}
Body-drain diode reverse recovery time	t_{rr}	—	210	—	ns	$I_F = 4.4 \text{ A}$
Body-drain diode reverse recovery current	I_{rr}	—	14.5	—	A	$V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{S}$ ^{Note5}
Body-drain diode reverse recovery charge	Q _{rr}	—	1.7	—	μC	

Notes: 5. Pulse test

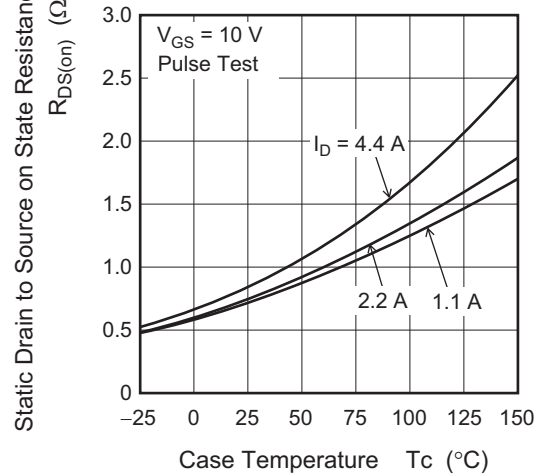
Main Characteristics



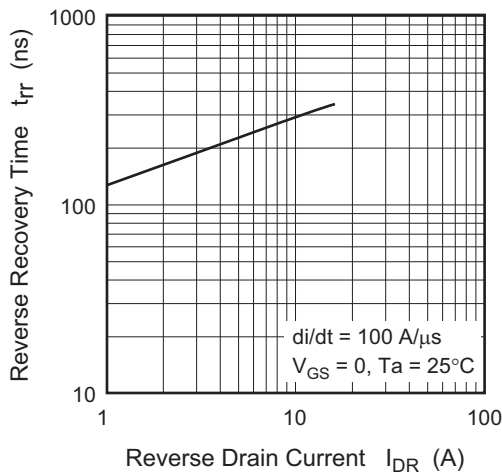
Static Drain to Source on State Resistance vs. Drain Current (Typical)



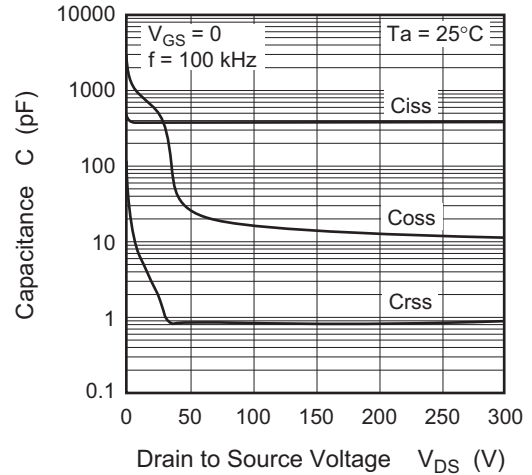
Static Drain to Source on State Resistance vs. Temperature (Typical)



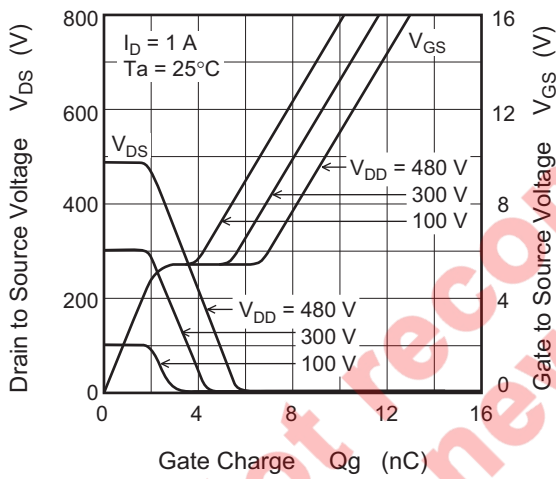
Body-Drain Diode Reverse Recovery Time (Typical)



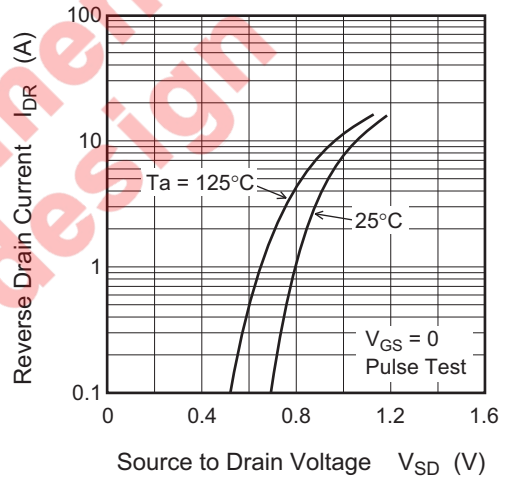
Typical Capacitance vs. Drain to Source Voltage



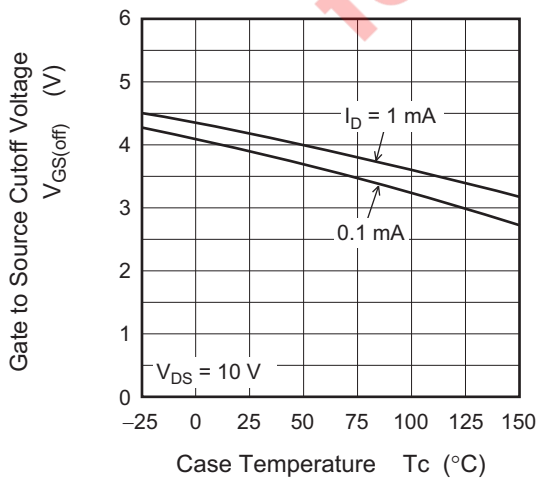
Dynamic Input Characteristics (Typical)



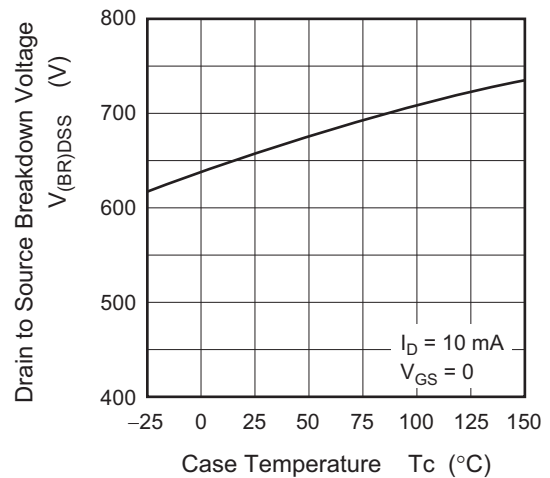
Reverse Drain Current vs. Source to Drain Voltage (Typical)



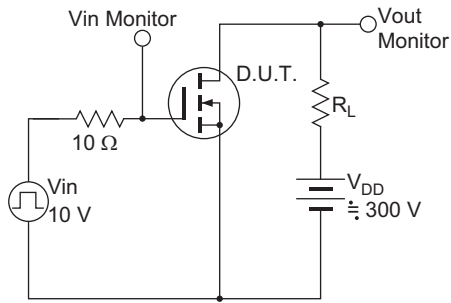
Gate to Source Cutoff Voltage vs. Case Temperature (Typical)



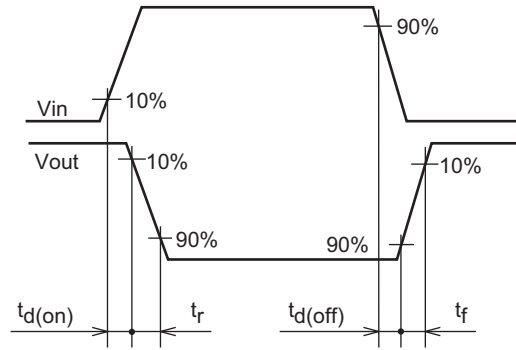
Drain to Source Breakdown Voltage vs. Case Temperature (Typical)



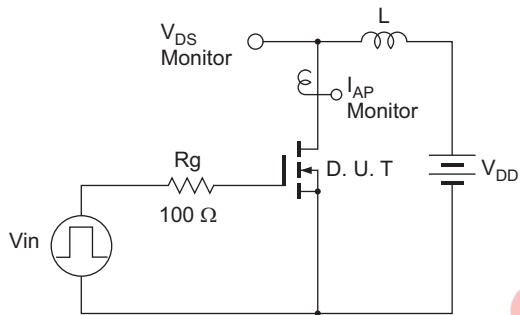
Switching Time Test Circuit



Waveform

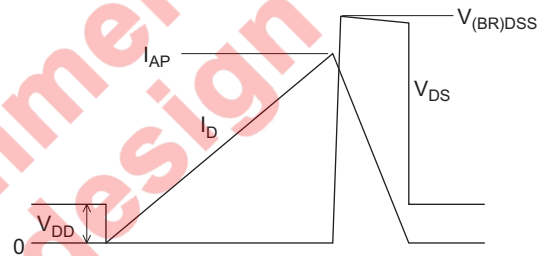


Avalanche Test Circuit



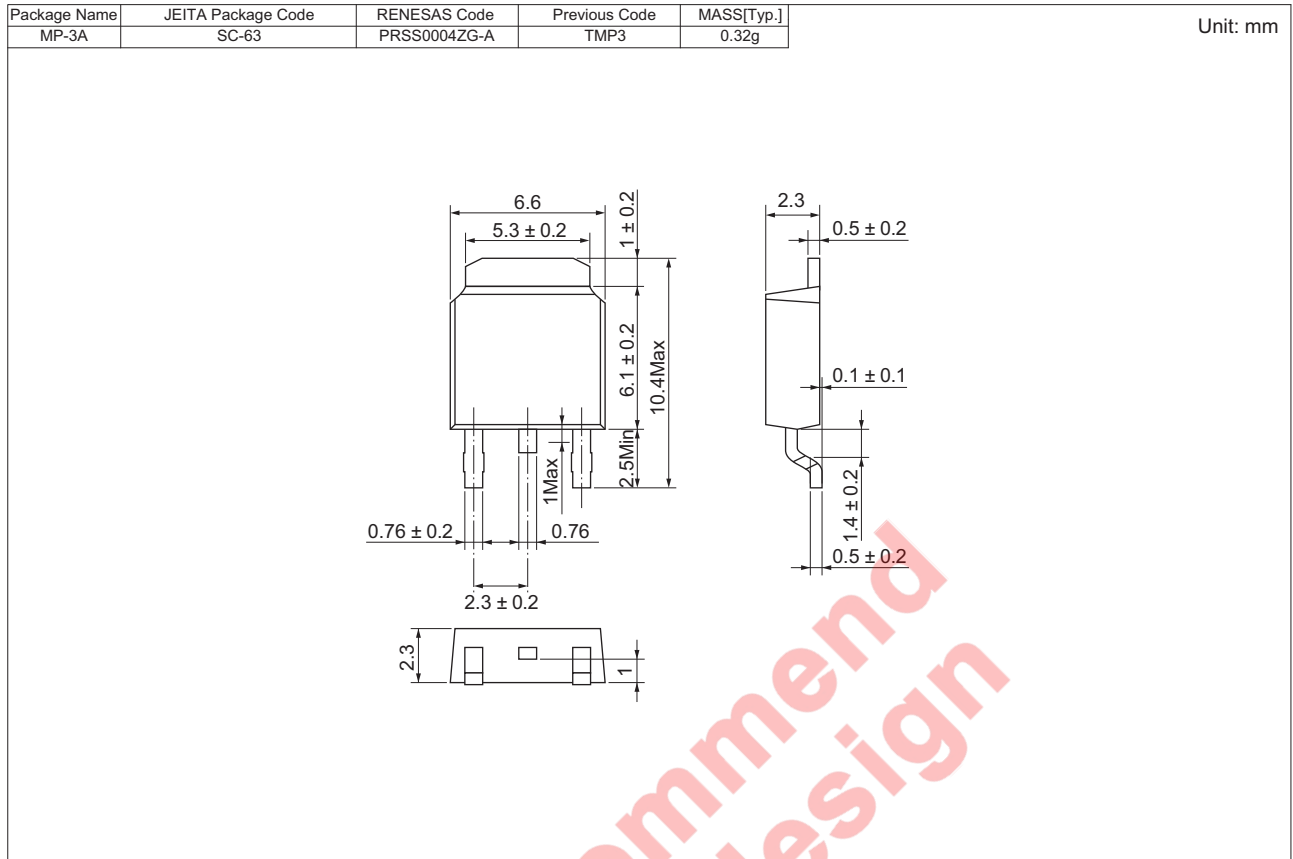
Avalanche Waveform

$$E_{AR} = \frac{1}{2} L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



Not recommended for new design

Package Dimension



Ordering Information

Orderable Part No.	Quantity	Shipping Container
RJK60S1DPD-00#J2	3000 pcs	Taping

Not recommend
for new design

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